

Application Serial No.: 10/637,146
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In the Summary of the Invention:

- Please amend the paragraph starting on page 3, line 2, as follows:

The present invention is directed to an area efficient, temperature-insensitive bias circuit for high-power amplifiers. In one exemplary embodiment, a bias circuit is coupled to an amplifier, such as an RF amplifier, and comprises a first bipolar transistor, a second bipolar transistor and a third bipolar transistor. The first bipolar transistor has a base connected to a first node, and the first node is connected to a reference voltage through a first resistor. The second bipolar transistor has a base connected to the first node. The third bipolar transistor has a collector connected to the first node and a base connected to an emitter of the first bipolar transistor at a second node. An emitter of the second bipolar transistor is connected to a base of a fourth bipolar ~~transmitter~~ transistor associated with the amplifier, and the second bipolar transistor does not have a resistor connected to the emitter of the second bipolar transistor.